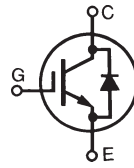


GenX3™ 600V IGBT with Diode

IXGH36N60A3D4

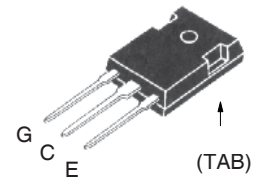
Ultra Low V_{sat} PT IGBT for
up to 5kHz switching



$$\begin{aligned} V_{CES} &= 600V \\ I_{C110} &= 36A \\ V_{CE(sat)} &\leq 1.4V \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_C = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C110}	$T_C = 110^\circ\text{C}$	36	A
I_{F110}	$T_C = 110^\circ\text{C}$	10	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	200	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 5\Omega$ Clamped inductive load @ $\leq 600V$	$I_{CM} = 60$	A
P_C	$T_C = 25^\circ\text{C}$	220	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		6.0	g

TO-247 (IXGH)



G = Gate C = Collector
E = Emitter TAB = Collector

Features

- Optimized for low conduction losses
- Square RBSOA
- Anti-parallel ultra fast diode
- International standard package

Advantages

- High power density
- Low gate drive requirement

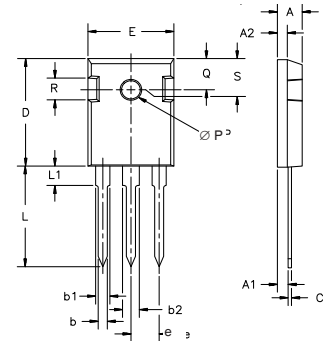
Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			75 μA 500 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 30A$, $V_{GE} = 15V$, Note 1			1.4 V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 30\text{A}$, $V_{CE} = 10\text{V}$, Note 1	25	42	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		2380	pF
C_{oes}			115	pF
C_{res}			30	pF
Q_g	$I_C = 30\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		80	nC
Q_{ge}			12	nC
Q_{gc}			36	nC
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ\text{C}$ $I_C = 30\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}$, $R_G = 5\Omega$		18	ns
t_{ri}			23	ns
E_{on}			0.74	mJ
$t_{d(off)}$			330	ns
t_{fi}			325	ns
E_{off}			3.00	mJ
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ\text{C}$ $I_C = 30\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}$, $R_G = 5\Omega$		18	ns
t_{ri}			25	ns
E_{on}			1.50	mJ
$t_{d(off)}$			500	ns
t_{fi}			500	ns
E_{off}			5.30	mJ
R_{thJC}			0.56	$^\circ\text{C/W}$
R_{thCS}			0.21	$^\circ\text{C/W}$

TO-247 (IXGH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

Reverse Diode (FRED)

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 10\text{A}$, $V_{GE} = 0\text{V}$, Note 1 $T_J = 150^\circ\text{C}$		1.7	3.0 V
I_{RM}	$I_F = 10\text{A}$, $-di_F/dt = 200\text{A}/\mu\text{s}$ $V_R = 300\text{V}$		60	ns
t_{rr}				3 A
				4 A
R_{thJC}				2.5 $^\circ\text{C/W}$

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ 25°C

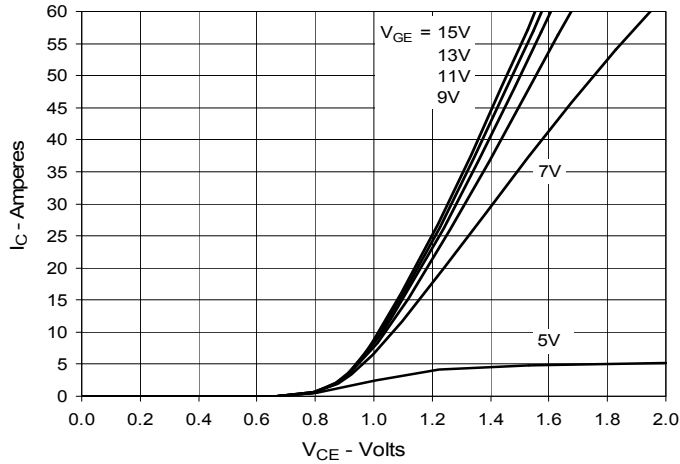


Fig. 2. Extended Output Characteristics
@ 25°C

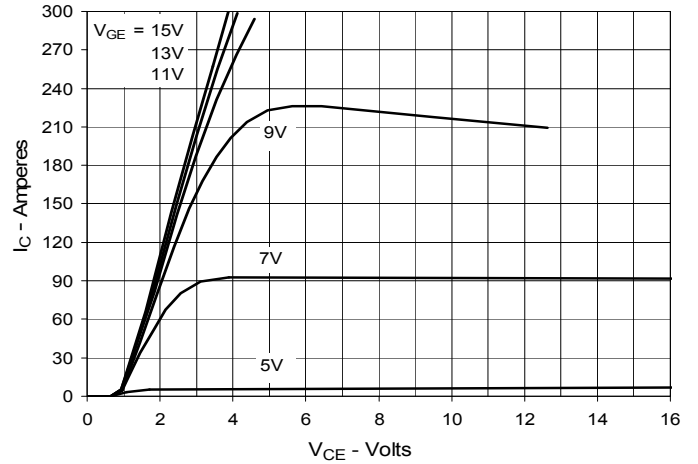


Fig. 3. Output Characteristics
@ 125°C

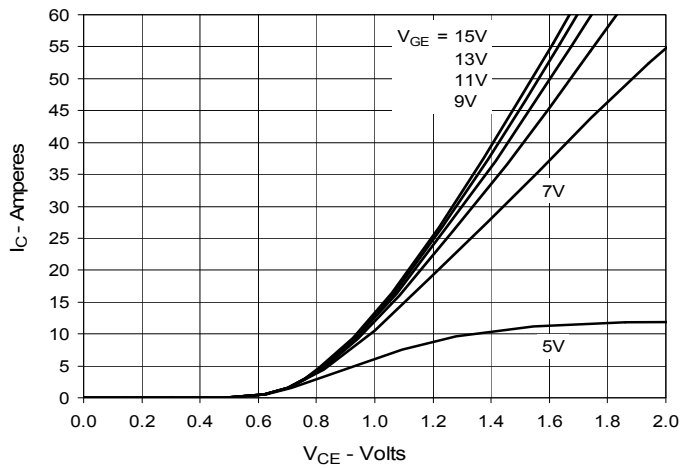


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

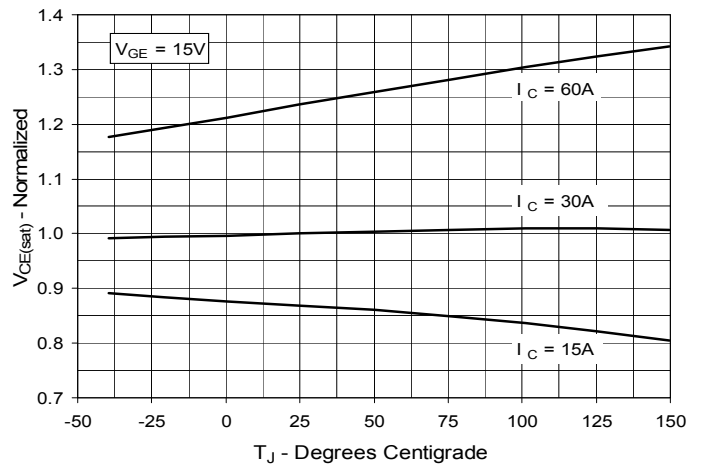


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

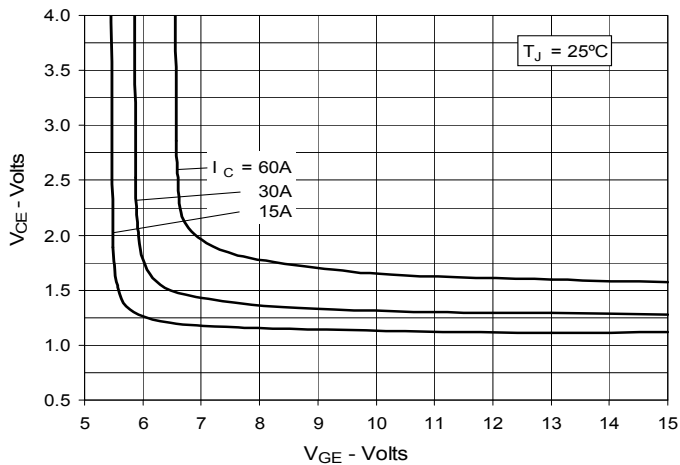


Fig. 6. Input Admittance

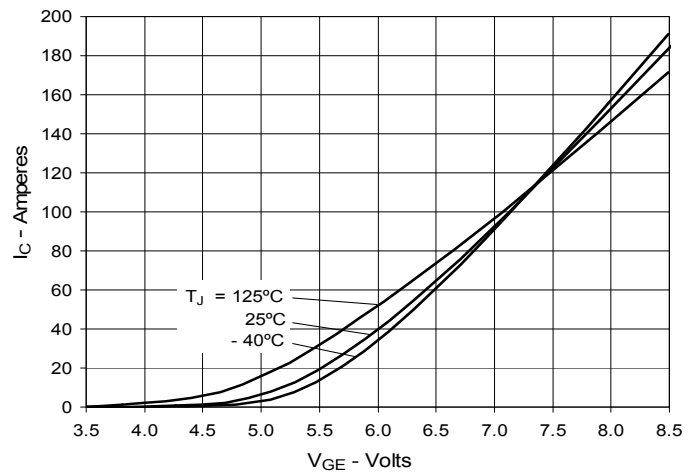


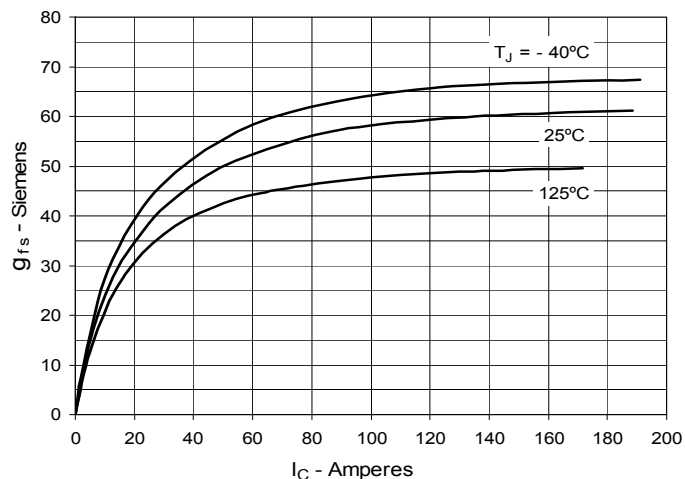
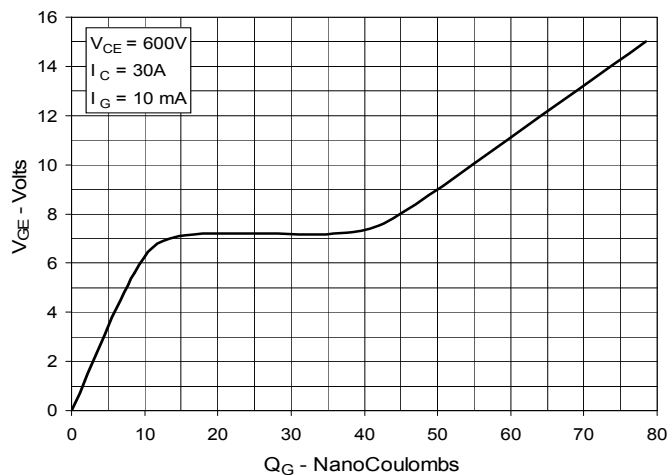
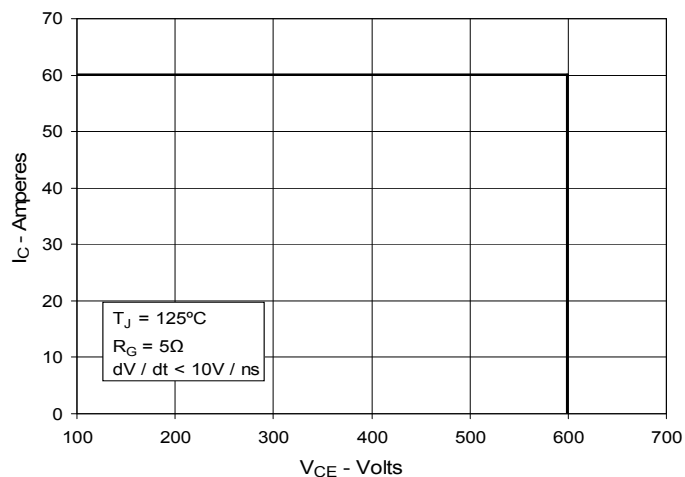
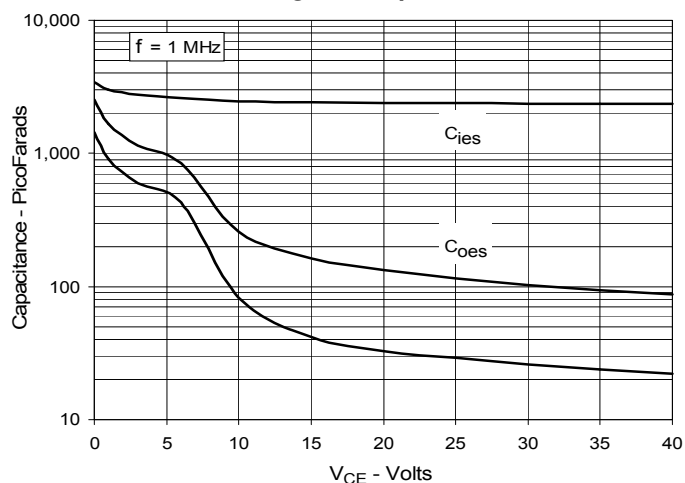
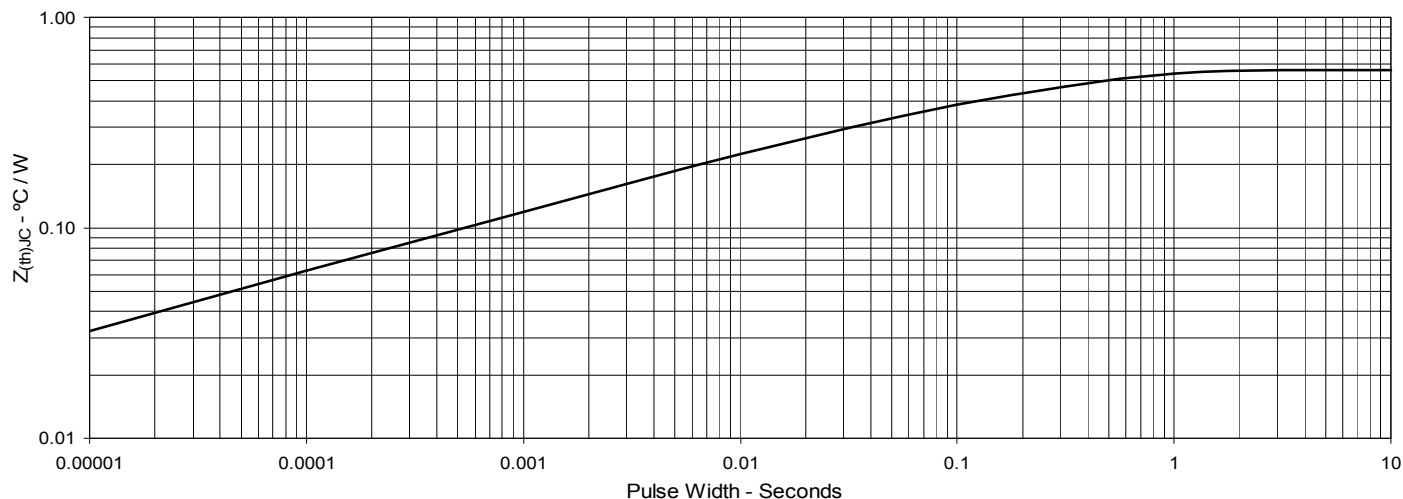
Fig. 7. Transconductance

Fig. 17. Gate Charge

Fig. 19. Reverse-Bias Safe Operating Area

Fig. 18. Capacitance

Fig. 11. Maximum Transient Thermal Impedance


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

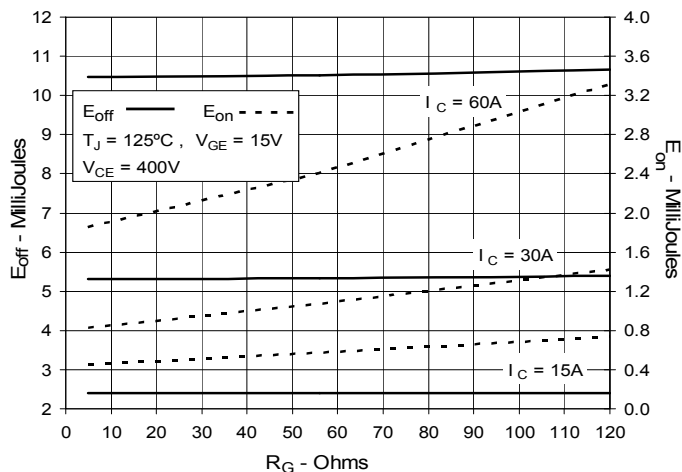


Fig. 13. Inductive Switching Energy Loss vs. Junction Temperature

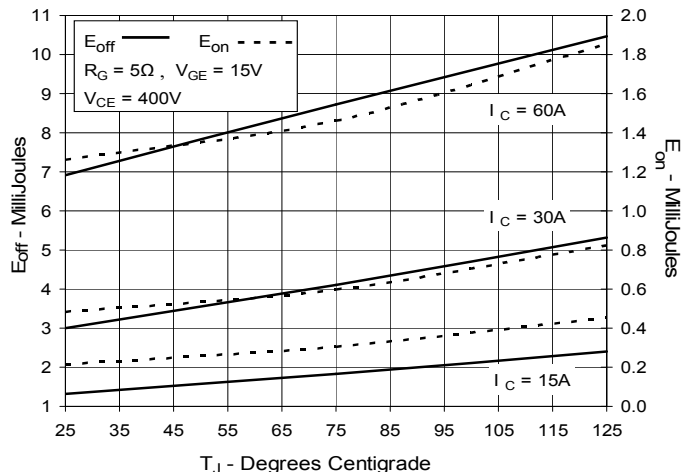


Fig. 14. Inductive Switching Energy Loss vs. Collector Current

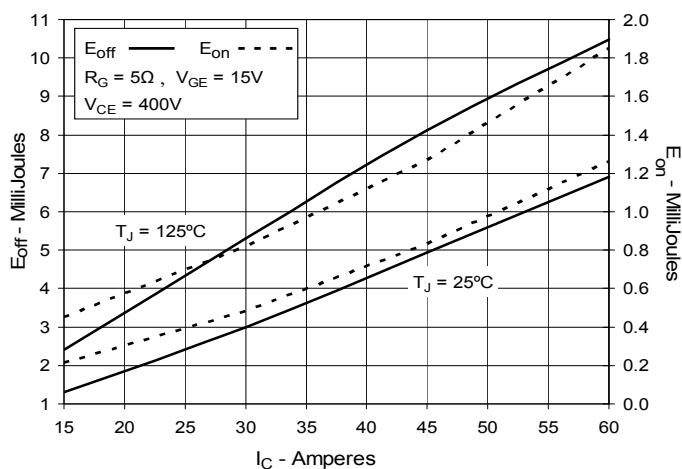


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

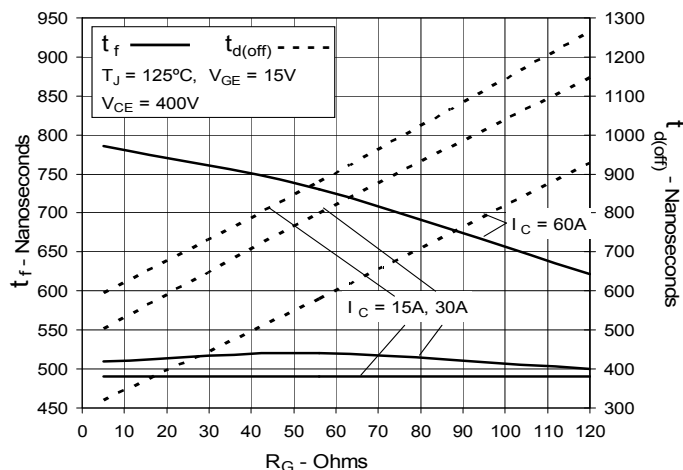


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

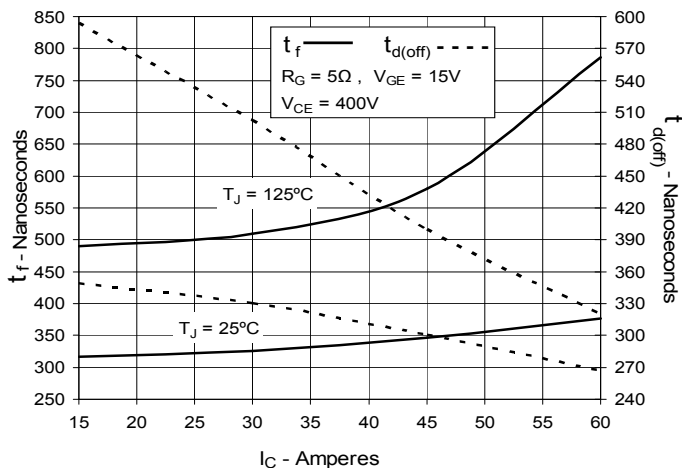


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

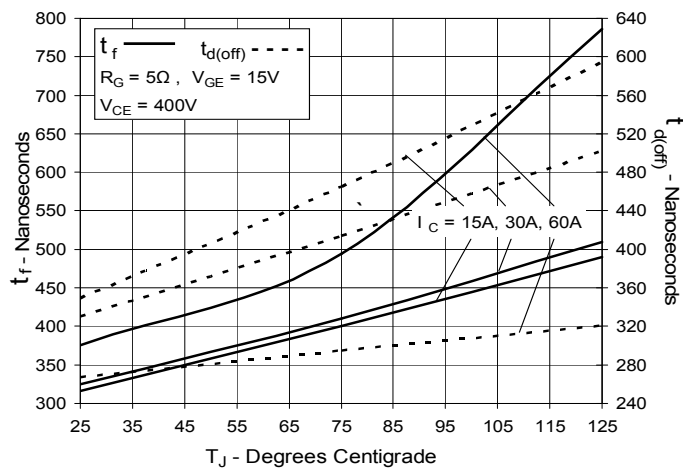


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

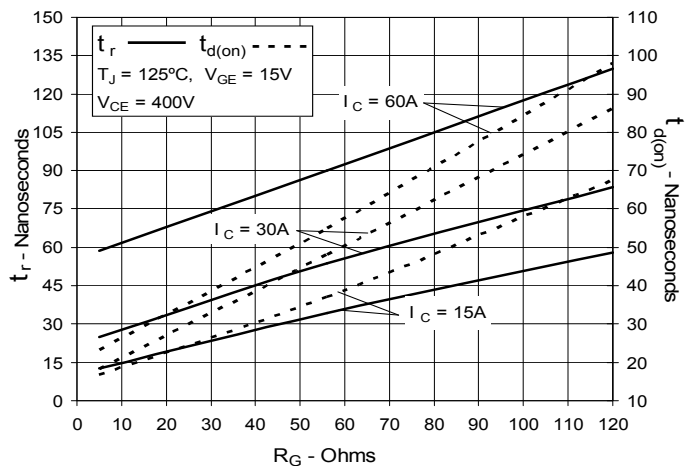


Fig. 19. Inductive Turn-on Switching Times vs. Junction Temperature

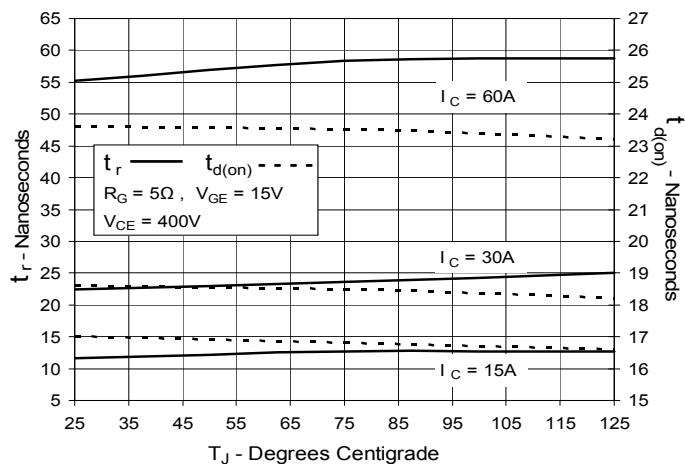
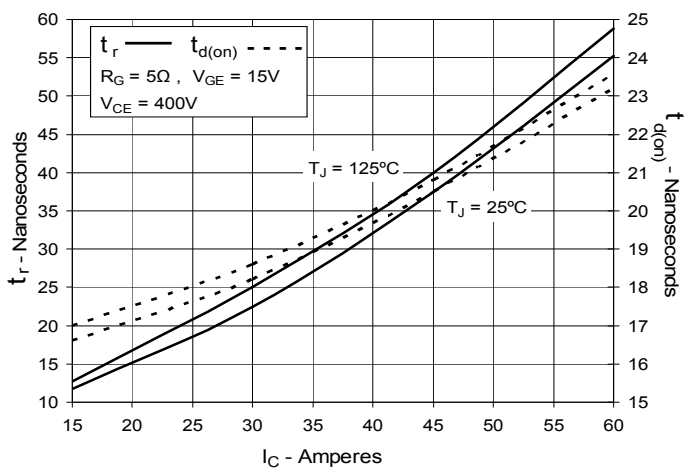


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current



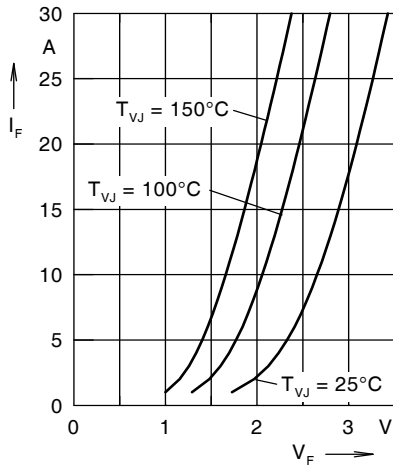


Fig. 21. Forward current I_F versus V_F

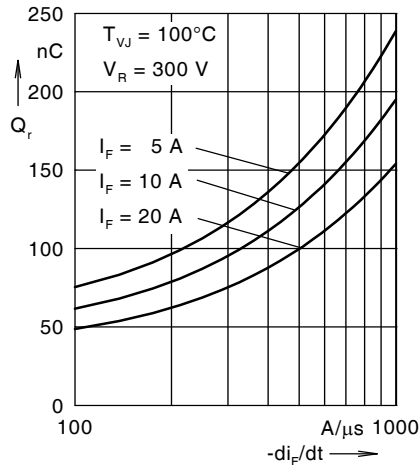


Fig. 22. Reverse recovery charge Q_r

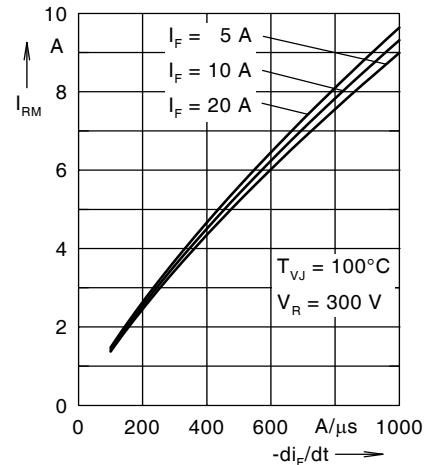


Fig. 23. Peak reverse current I_{RM}

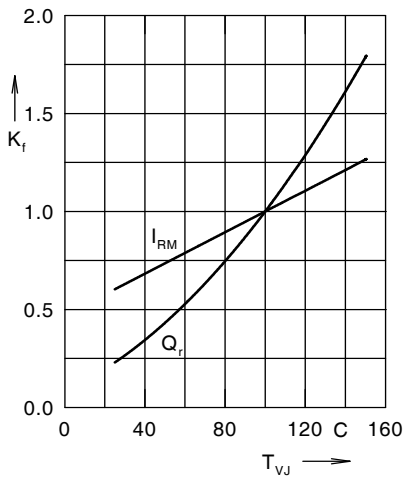


Fig. 24. Dynamic parameters Q_r , I_{RM}

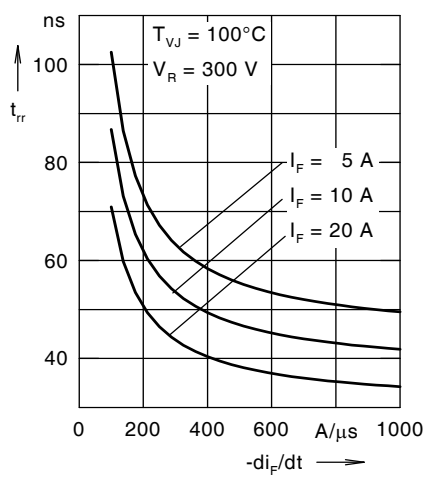


Fig. 25. Recovery time t_{rr} versus $-di_F/dt$

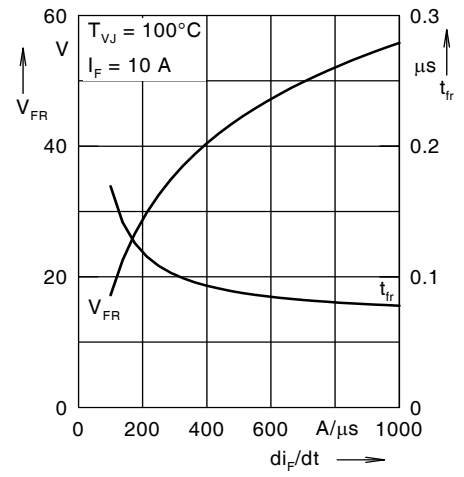


Fig. 26. Peak forward voltage V_{FR} and

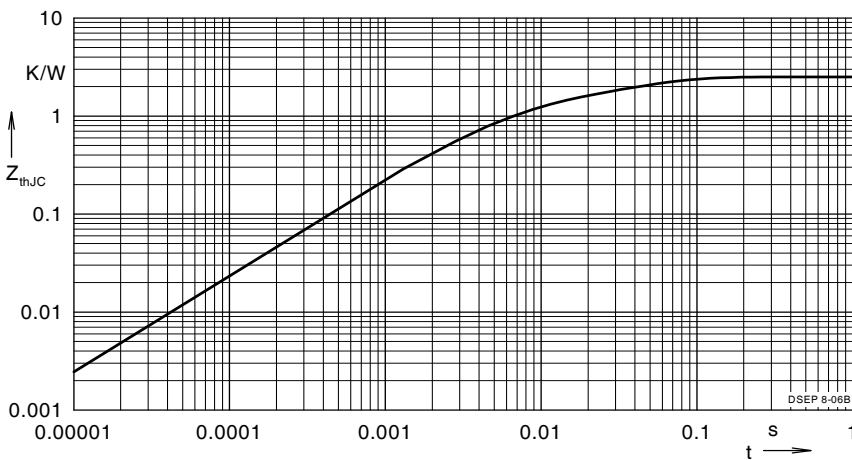


Fig. 27. Transient thermal resistance junction-to-case

NOTE: Fig. 2 to Fig. 6 shows typical values

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	1.449	0.0052
2	0.5578	0.0003